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IGBT/SiC MOSFET driver power supply



FEATURES

- High efficiency up to 88%
- Isolation voltage up to 5000VAC (reinforced insulation)
- The maximum capacitive load is 200uF
- Isolation capacitor 3.5pF typ.
- Operating temperature range: -40°C to +105°C
- Product material conforms to CTI Class I
- Designed for 1700V IGBT/SiC MOSFET driver

The IGBT/SIC MOSFET driver power supply series is a DC-DC module power supply specially designed for 1700 V IGBT/SIC MOSFET drivers. The product is dual isolated and dual positive output. It has output short-circuit protection and self-recovery. Both input and output meet the reinforced insulation design, complying with UL62368, EN62368, EN50178 standard certification. This product is suitable for: 1. Universal converter

- 2. AC servo drive system
- 3. Electric welding machine
- 4. Un-interruptible power supply (UPS)

Selection Guide							
Certification	Part No.	Input		Output		Full Load	Max.
		Voltage(VDC) (Range)	Current(mA, Typ.) Full Load/No Load	Voltage (VDC) +Vo1/+Vo2	Current (mA) +lo1/+lo2	Efficiency (%) Typ.	Capacitive Load(µF)
	QA123D-2GR3	12(10.80-13.20)	450/25	24/24 100/100	100/100 85/88		
EN	QA153D-2GR3	15(13.50-16.50)	360/20			85/88	200
	QA243D-2GR3	24(21.60-26.40)	230/15				

Input Specifications Operating Conditions Min. Unit Item Typ. Max. QA123D-2GR3 DC -0.7 ___ 18 QA153D-2GR3 DC VDC Input Voltage -0.7 23 ---QA243D-2GR3 DC -0.7 36 ___ Capacitance Filter Input Filter Hot Plug Unavailable

Note: Input end of QA243D-2GR3 shall be connected with 27μ F/63V electrolytic capacitor.

Output Specifications

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Item		Operating Conditions		Min.	Тур.	Max.	Unit		
Output QA153D Voltage 2GR3	QA123D-	+Vo1	Vin=12VDC, Pin14& Pin13	3 +lo= +100mA	22.80	24.00	25.20		
	2GR3	+Vo2	Vin=12VDC, Pin11& Pin12	Vin=12VDC, Pin11& Pin12 +lo= +100mA		24.00	25.20		
	QA153D-	+Vo1	Vin=15VDC, Pin14& Pin13 +lo= +100mA		22.80	24.00	25.20		
	2GR3	+Vo2	Vin=15VDC, Pin11& Pin12	2 +lo= +100mA	22.80	24.00	25.20	VDC	
	QA243D-	+Vo1	Vin=24VDC, Pin14& Pin13 +lo= +100mA 22.80		24.00	25.20			
	2GR3	+Vo2	Vin=24VDC, Pin11& Pin12	2 +lo= +100mA	22.80	24.00	25.20		
Output Power		Vin=typ. 100% load			4.80		W		
Voltage A	Accuracy		10% - 100% load		See out	put regulatio	n curve (Fig.	1,Fig. 2)	
Linear Regulation		Full wold and have a second and and	Vo1 Output			±1.5			
		Full voltage input range	Vo2 Output			±1.5			
Load Regulation		QA123D-2GR3	Vo1 Output		15		%		
		10%-100% load	Vo2 Output		15		70		

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DC/DC Converter IGBT/SiC MOSFET Driver Power Supply Series



	QA153D-2GR3	Vo1 Output		12		
	QA243D-2GR3 10%-100% load	Vo2 Output		12		
Temperature Coefficient	Full load				±0.1	%/ ℃
Ripple & Noise*	20MHz bandwidth			100	250	mVp-p
Short-circuit Protection	ort-circuit Protection			Continuous,	self-recovery	

Note:* The "parallel cable" method is used for Ripple and Noise test, please refer to DC-DC Converter Application Notes for specific information.

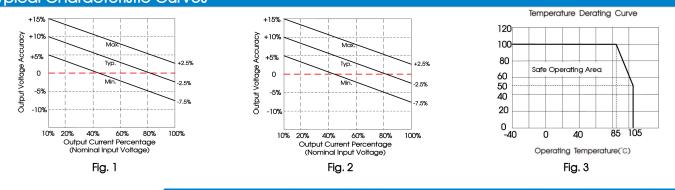
General Specification	S				
Item	Operating Conditions	Min.	Тур.	Max.	Unit
Isolation	Input-output, output 1- output 2, Test for 1 minute with a leakage current of 1mA max (reinforced insulation)	5000			VAC
Continuous insulation voltage (complying with EN61800-5-1)	Input- output 1, Input- output 2	1700			VDC
Insulation Resistance	Input-output resistance at 500VDC	1000			MΩ
Isolation capacitor Input- output 1, Input- output 2, output 1- output 2 capacitor at 100kHz/0.1V			3.5	5	pF
Electrical clearance	Input- output	24.30	24.90		mm
	Output 1- output 2	14.14	14.74		mm
•	Input- output	24.30	24.90		mm
Creepage distance	Output 1- output 2	14.14	14.74		mm
Operating Temperature	Derating when operating temperature \ge 85 °C , (see Fig. 3)	-40		105	
Storage Temperature		-55		125	ۍ ا
Pin Soldering Resistance Temperature	Soldering spot is 1.5mm away from case for 10 seconds			300	
Case Temperature Rise	e Temperature Rise Ta=25°C , nominal input voltage , full load		30	60	
Safety Standard		EN62368-1 (I	Report)		
Storage Humidity	Non-condensing	5		95	%RH
Switching Frequency	Full load, nominal input voltage		200		kHz
MTBF	MIL-HDBK-217F@25℃	3500			k hours

Mechanical Specifications				
Case Material	Black plastic; flame-retardant and heat-resistant			
CTI level	roduct material conforms to CTI Class I			
Dimensions	31.60 x 20.30 x 10.20mm			
Weight	12g(Тур.)			
Cooling Method	Free air convection			

Electromagnetic Compatibility (EMC)				
CE	CE	CISPR32/EN55032 CLASS A (see Fig.6 for recommended circuit)		
Emissions	RE	CISPR32/EN55032 CLASS A (see Fig.6 for recommended circuit)		
Immunity	ESD	IEC/EN61000-4-2 Contact ±6kV perf. Criteria A		

Typical Characteristic Curves

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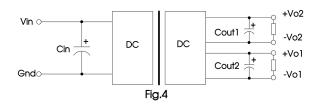


Design Reference

1. Typical application

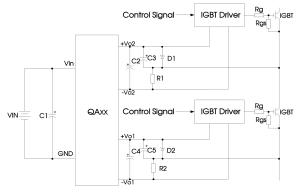
All driver power in this series are tested according to the recommended test circuit (Figure 4) before they leave the factory, with both outputs connected to the same load.

Input and/or output ripple can be further reduced by appropriately increasing the input & output capacitor values Cin and Cout and/or by selecting capacitors with a low ESR (equivalent series resistance). Also make sure that the capacitance is not exceeding the max. capacitive load value of the product.



Vin	12/15/24V
Cin	100µF
Cout1	100µF
Cout2	100µF

2. Typical application



C1	100µF/63V
C2、C3、C4、C5	100µF/35V
R1、R2	15k Ω
D1、D2	15V/18V/20V

Fig. 5

Application Notes

1. The wire between the converter and IGBT driver must as short as possible.

2. External filter capacitors should be connected as close as possible to the IGBT driver.

- 3. To ensure the high peak gate current, the filter capacitors should be electrolytic capacitor and ceramic capacitor collocation.
- 4. The output average power of the IGBT driver should be less than the output power of DC-DC module.

5. SiC MOSFET driver application circuit can refer to the above design.

3. EMC compliance circuit

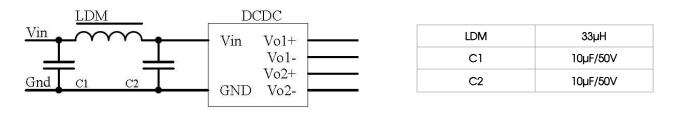


Fig. 6

4. Electrolytic capacitors are recommended for external capacitors at the input or output of the product. Tantalum capacitors are not, otherwise there is a risk of failure.

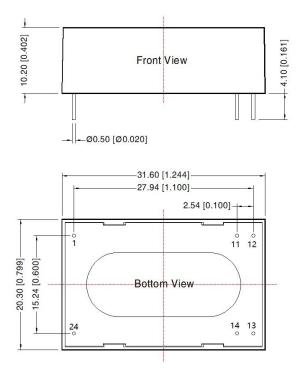
5. The products do not support parallel connection of their output or hot-plug use.

6. For additional information please refer to the application notes on www.mornsun-power.com

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Dimensions and Recommended Layout



Ø1.00 [Ø0.039]

Note: Grid 2.54*2.54mm

Pin-Out				
Pin	Mark			
1	GND			
11	Vo2+			
12	Vo2-			
13	Vo1-			
14	Vo1+			
24	Vin			

Note: Unit: mm[inch] Pin diameter tolerances: ±0.10[±0.004] General tolerances: ±0.50[±0.020]

Notes:

- 1. For additional information on Product Packaging please refer to <u>www.mornsun-power.com.</u> Packaging bag number: 58210008;
- 2. The lead wire connecting the power module and IGBT driver (or SiC MOSFET driver) should be as short as possible when in use;
- 3. The output filter capacitor is as close as possible to the power module and IGBT driver (or SiC MOSFET driver);
- 4. IGBT driver (or SiC MOSFET driver) gate drive current has a high peak value. It is recommended that the output filter capacitor of the power module use a low internal resistance electrolytic capacitor;
- 5. The average output power of the driver must be lower than that of the power supply module;
- 6. Consider fixing with glue near the module if being used in vibration occasion;
- 7. The maximum capacitive load offered were tested at nominal input voltage and full load;
- 8. Unless otherwise specified, parameters in this datasheet were measured under the conditions of Ta=25°C, humidity<75%RH with nominal input voltage and rated output load;
- 9. All index testing methods in this datasheet are based on company corporate standards;
- 10. We can provide product customization service, please contact our technicians directly for specific information;
- 11. Products are related to laws and regulations: see "Features" and "EMC";
- 12. Our products shall be classified according to ISO14001 and related environmental laws and regulations, and shall be handled by qualified units.

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